

TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL MOS TYPE

GT8Q102(SM)

HIGH POWER SWITCHING APPLICATIONS

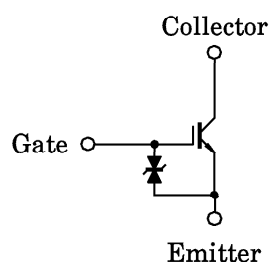
MOTOR CONTROL APPLICATIONS

Unit in mm

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V_{CES}	1200	V
Gate-Emitter Voltage		V_{GES}	± 20	V
Collector Current	DC	I_C	8	A
	1ms	I_{CP}	16	
Collector Power Dissipation	(Tc = 25°C)	P_C	50	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C

EQUIVALENT CIRCUIT



1. GATE	
2. COLLECTOR (HEAT SINK)	
3. EMITTER	
JEDEC	—
EIAJ	—
TOSHIBA	2-10S2C

Weight : 1.4g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	± 10	μA
Collector Cut-off Current		I_{CES}	$V_{CE} = 1200V, V_{GE} = 0$	—	—	1.0	mA
Gate-Emitter Cut-off Voltage		$V_{GE} (OFF)$	$V_{CE} = 5V, I_C = 8mA$	3.0	—	6.0	V
Collector-Emitter Saturation Voltage		$V_{CE} (sat)$	$I_C = 8A, V_{GE} = 15V$	—	3.0	4.0	V
Input Capacitance		C_{ies}	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	1000	—	pF
Switching Time	Rise Time	t_r		—	0.3	0.6	μs
	Turn-on Time	t_{on}		—	0.4	0.8	
	Fall Time	t_f		—	0.25	0.5	
	Turn-off Time	t_{off}		—	0.7	1.3	

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